

BUK768R1-100E,118 Datasheet



| DiGi Electronics Part Number | |
|------------------------------|--|
| Manufacturer | |
| Manufacturer Product Number | |
| Description | |

Detailed Description

BUK768R1-100E,118-DG

Nexperia USA Inc.

BUK768R1-100E,118

MOSFET N-CH 100V 100A D2PAK

N-Channel 100 V 100A (Tc) 263W (Tc) Surface Moun t D2PAK

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Purchase and inquiry

| Manufacturer Product Number: | Manufacturer: |
|---|---|
| BUK768R1-100E,118 | Nexperia USA Inc. |
| Series: | Product Status: |
| TrenchMOS™ | Obsolete |
| FET Type: | Technology: |
| N-Channel | MOSFET (Metal Oxide) |
| Drain to Source Voltage (Vdss): | Current - Continuous Drain (Id) @ 25°C: |
| 100 V | 100A (Tc) |
| Drive Voltage (Max Rds On, Min Rds On): | Rds On (Max) @ ld, Vgs: |
| 10V | 8.1mOhm @ 25A, 10V |
| Vgs(th) (Max) @ ld: | Gate Charge (Qg) (Max) @ Vgs: |
| 4V @ 1mA | 108 nC @ 10 V |
| Vgs (Max): | Input Capacitance (Ciss) (Max) @ Vds: |
| ±20V | 7380 pF @ 25 V |
| FET Feature: | Power Dissipation (Max): |
| | 263W (Tc) |
| Operating Temperature: | Grade: |
| -55°C ~ 175°C (TJ) | Automotive |
| Qualification: | Mounting Type: |
| AEC-Q101 | Surface Mount |
| Supplier Device Package: | Package / Case: |
| D2PAK | TO-263-3, D2PAK (2 Leads + Tab), TO-263AB |
| Base Product Number: | |
| BUK768 | |
| | |

Environmental & Export classification

| RoHS Status: | Moisture Sensitivity Level (MSL): |
|------------------|-----------------------------------|
| ROHS3 Compliant | 1 (Unlimited) |
| REACH Status: | ECCN: |
| REACH Unaffected | EAR99 |
| HTSUS: | |
| 8541.29.0095 | |



BUK768R1-100E

N-channel TrenchMOS standard level FET 5 October 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

| Table 1. C | | | | | | | |
|-------------------|----------------------------------|---|-----|-----|------|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u> | [1] | - | - | 100 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 263 | W |
| Static chara | acteristics | · | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | | - | 6.4 | 8.1 | mΩ |
| Dynamic ch | haracteristics | · | | | | | |
| Q _{GD} | gate-drain charge | V_{GS} = 10 V; I _D = 25 A; V _{DS} = 80 V; T _j = 25 °C; Fig. 13; Fig. 14 | | - | 38.6 | - | nC |

Table 1. Quick reference data

[1] Continuous current is limited by package.

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2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | mb | D |
| 2 | D | drain | | |
| 3 | S | source | | G-UT 4 |
| mb | D | mounting base; connected to drain | | mbb076 S |
| | | | D2PAK (SOT404) | |

3. Ordering information

| Table 3. Ordering inf | formation | | |
|-----------------------|-----------|--|---------|
| Type number | Package | | |
| | Name | Description | Version |
| BUK768R1-100E | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Marking

| Table 4. Marking codes | |
|------------------------|---------------|
| Type number | Marking code |
| BUK768R1-100E | BUK768R1-100E |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|---------|-------------------|-------------------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | 100 | V |
| V _{DGR} | drain-gate voltage | R _{GS} = 20 kΩ | | - | 100 | V |
| V _{GS} | gate-source voltage | T _j ≤ 175 °C; DC | | -20 | 20 | V |
| I _D | drain current | T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u> | [1] | - | 100 | А |
| | | T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u> | | - | 78 | А |
| I _{DM} | peak drain current | T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4 | | - | 439 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 2</u> | | - | 263 | W |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
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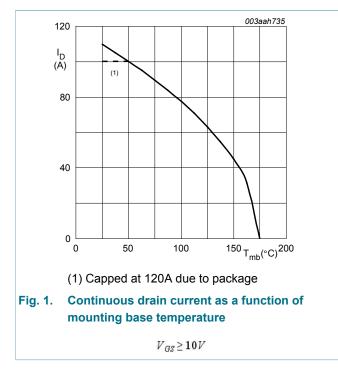
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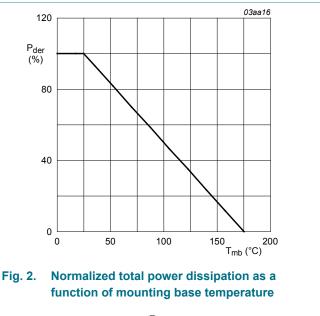
| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|---|--|--------|-----|-----|------|
| Source-drain | Source-drain diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [1] | - | 100 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 439 | А |
| Avalanche ru | ggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\label{eq:ID} \begin{array}{l} I_{D} = 100 \; \text{A}; V_{sup} \leq 100 \; \text{V}; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(init)} = 25 \; ^{\circ}\text{C}; \; \text{unclamped}; \\ \hline \text{Fig. 3} \end{array}$ | [2][3] | - | 219 | mJ |

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

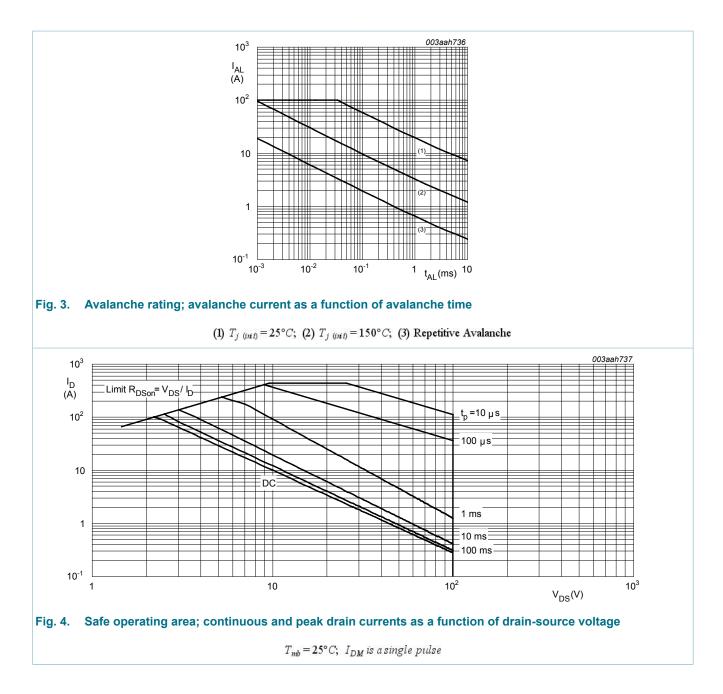




$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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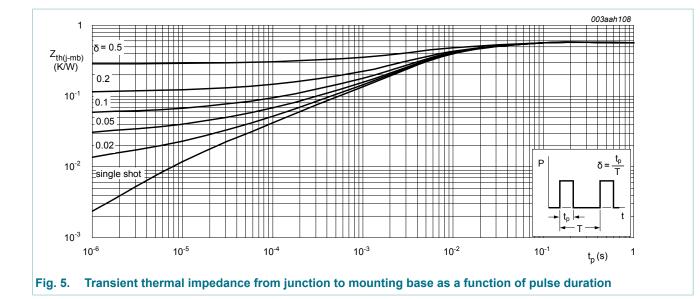


6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|--|-----|-----|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 5</u> | - | - | 0.57 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint ; mounted on a printed-circuit board | - | 50 | - | K/W |

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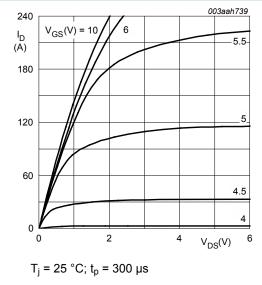
Characteristics 7.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|----------------------------------|---|-----|------|------|------|
| Static chara | acteristics | 1 | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C | 100 | - | - | V |
| | breakdown voltage | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 90 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 4.5 | V |
| I _{DSS} drain | drain leakage current | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.02 | 1 | μA |
| | | V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | - | 6.4 | 8.1 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12 | - | - | 21.9 | mΩ |
| Dynamic ch | naracteristics | · · · | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 108 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | - | 22.8 | - | nC |
| Q _{GD} | gate-drain charge | | - | 38.6 | - | nC |

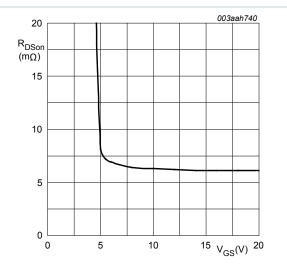
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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|------------------------------|---|---|-----|------|------|------|
| C _{iss} | input capacitance | V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; | | - | 5535 | 7380 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | | - | 521 | 625 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 352 | 482 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 80 V; R _L = 3.2 Ω; V _{GS} = 10 V; | | - | 23.5 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | | - | 44.1 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 72 | - | ns |
| t _f | fall time | | | - | 49.6 | - | ns |
| L _D | internal drain inductance | from upper edge of mounting base to centre of die | | - | 2.5 | - | nH |
| L _S | internal source inductance | measured from source lead to source bond pad ; $T_j = 25 \ ^{\circ}C$ | | - | 7.5 | - | nH |
| Source-dra | in diode | | I | | | | |
| V _{SD} | source-drain voltage | I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; Fig. 16 | | - | 0.82 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V; | | - | 55 | - | ns |
| Qr | recovered charge | V _{DS} = 25 V | | - | 134 | - | nC |





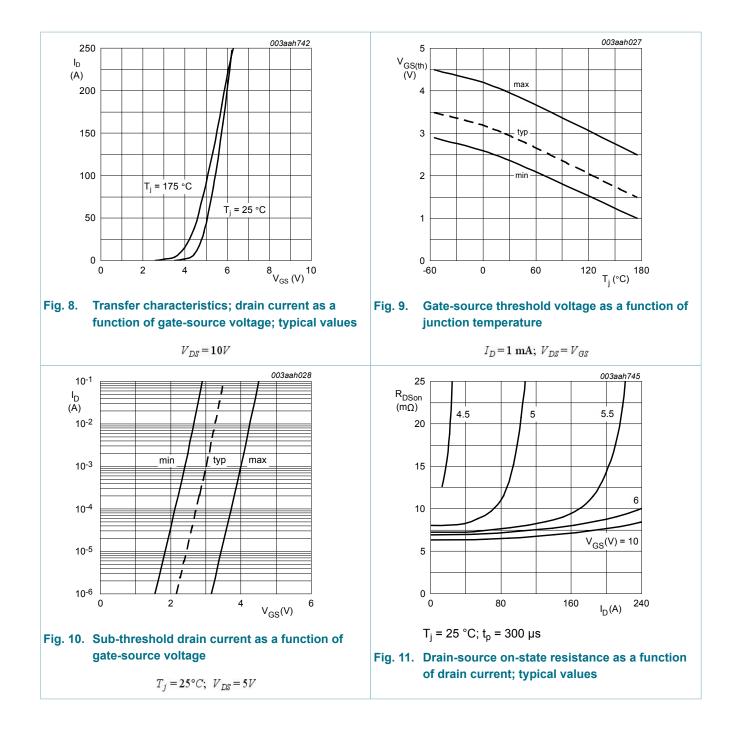




 $T_j = 25^{\circ}C; \ I_D = 25A$

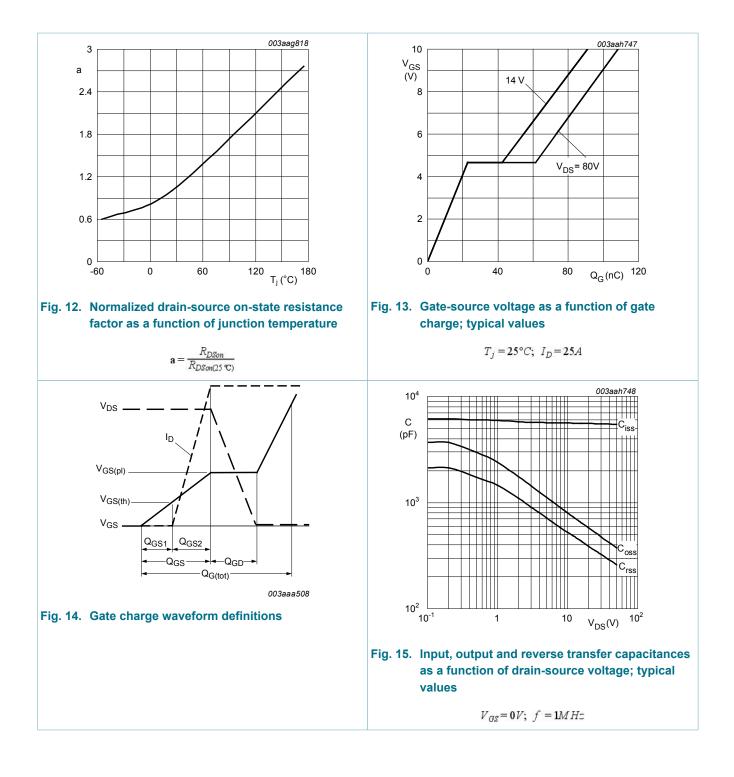
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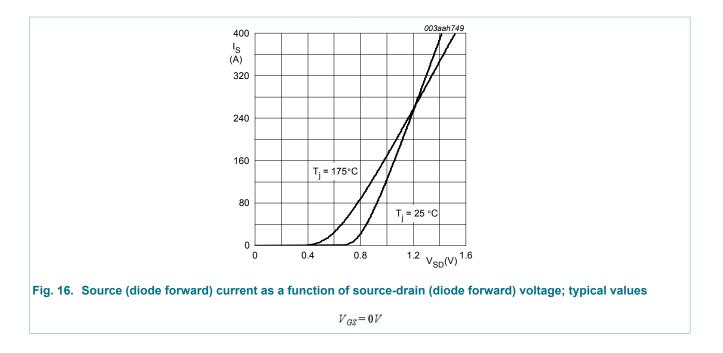
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8. Package outline

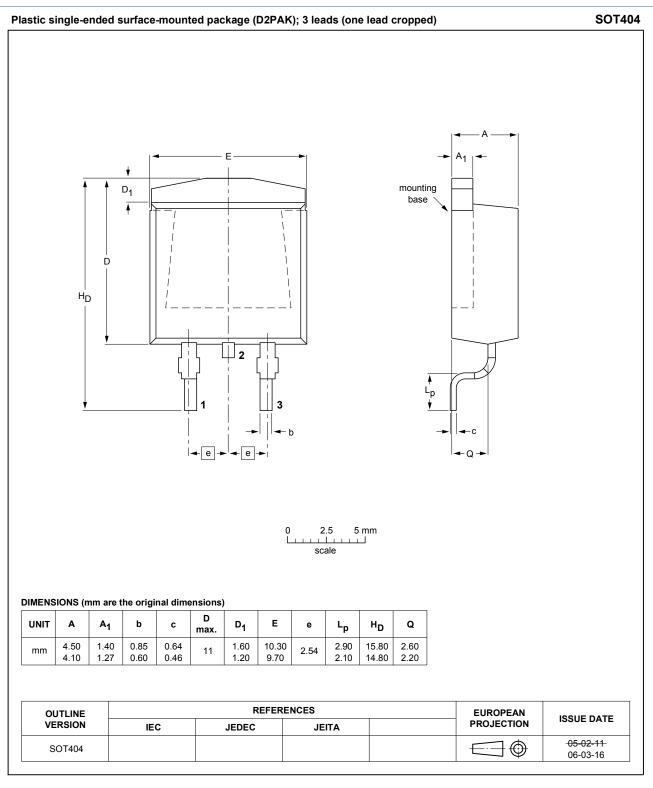


Fig. 17. Package outline D2PAK (SOT404)

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9. Legal information

9.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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